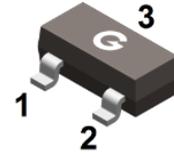
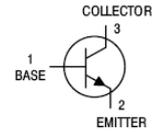


Features

- Epitaxial planar die construction
- Complimentary to BCX17
- Ultra-small surface mount package

HF



SOT-23

Mechanical Data

- Case: SOT-23
- Molding compound: UL flammability classification rating 94V-0
- Terminals: Tin-plated; solderability per MIL-STD-202, Method 208

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
BCX19	SOT-23	3000 pcs / Tape & Reel	U1

Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Base Breakdown Voltage	V _{CBO}	50	V
Collector-Emitter Breakdown Voltage	V _{CEO}	45	V
Emitter-Base Breakdown Voltage	V _{EBO}	5	V
Collector Current (Continuous)	I _C	0.5	A
Collector Current (Peak)	I _{CM}	1	A

Thermal Characteristics

Parameter	Symbol	Value	Unit
Power Dissipation	P _D	0.25	W
Thermal Resistance Junction-to-Air ^{**1}	R _{θJA}	280	°C/W
Thermal Resistance Junction-to-Case ^{**1}	R _{θJC}	160	°C/W
Thermal Resistance Junction-to-Lead ^{**1}	R _{θJL}	210	°C/W
Junction Temperature Range	T _J	-55 ~ +150	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

Note 1: The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 100\mu\text{A}, I_E = 0$	50	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10\text{mA}, I_B = 0$	45	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu\text{A}, I_C = 0$	5	-	-	V
Collector Cut-off Current	I_{CBO}	$V_{CB} = 20\text{V}, I_E = 0$	-	-	0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 5\text{V}, I_C = 0$	-	-	0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = 1\text{V}, I_C = 100\text{mA}$	100	-	600	-
		$V_{CE} = 1\text{V}, I_C = 300\text{mA}$	70	-	-	-
		$V_{CE} = 1\text{V}, I_C = 500\text{mA}$	40	-	-	-
Collector-emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$	-	-	0.62	V
Base-emitter On Voltage	$V_{BE(on)}$	$V_{CE} = 1\text{V}, I_C = 500\text{mA}$	-	-	1.2	V
Transition Frequency	f_T	$I_C = 10\text{mA}, V_{CE} = 5\text{V}$ $f = 100\text{MHz}$	100	-	-	MHz
Collector Output Capacitance	C_{OBO}	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$	-	5	-	pF

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

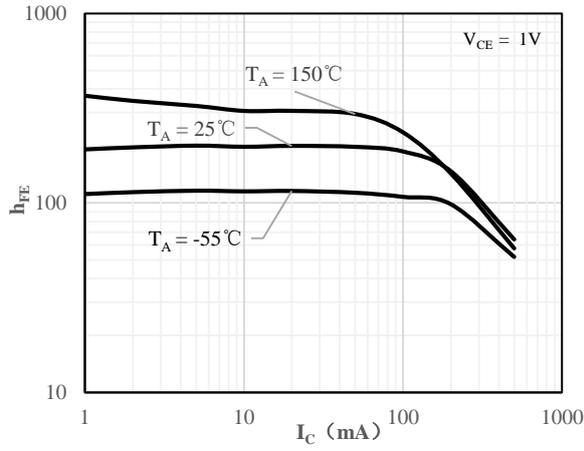


Fig 1 h_{FE} vs. I_C

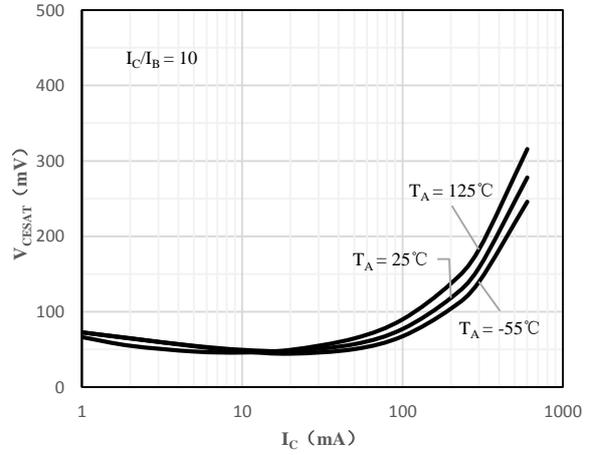


Fig 2 $V_{CE(sat)}$ vs. I_C

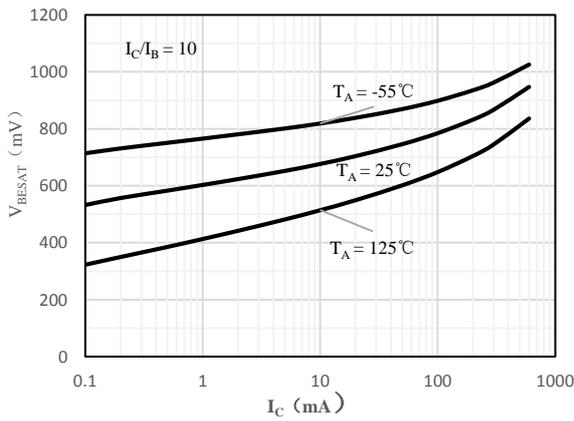


Fig 3 $V_{BE(sat)}$ vs. I_C

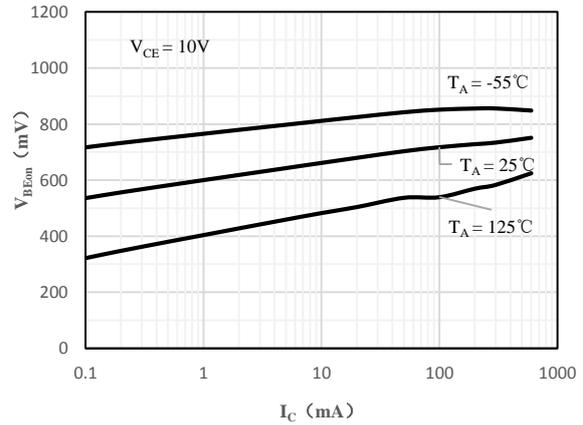
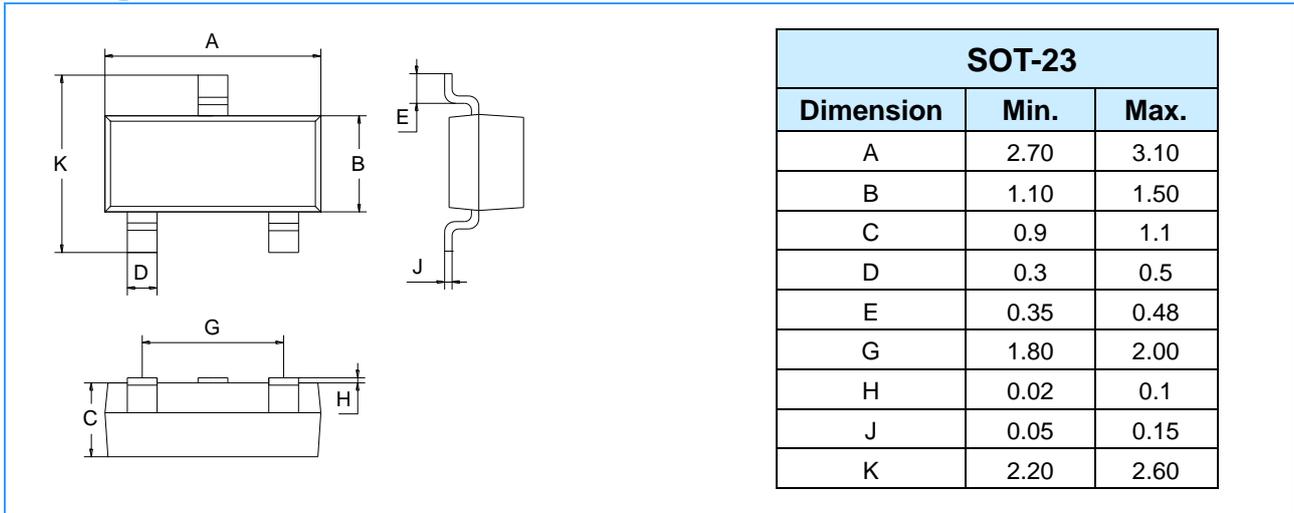
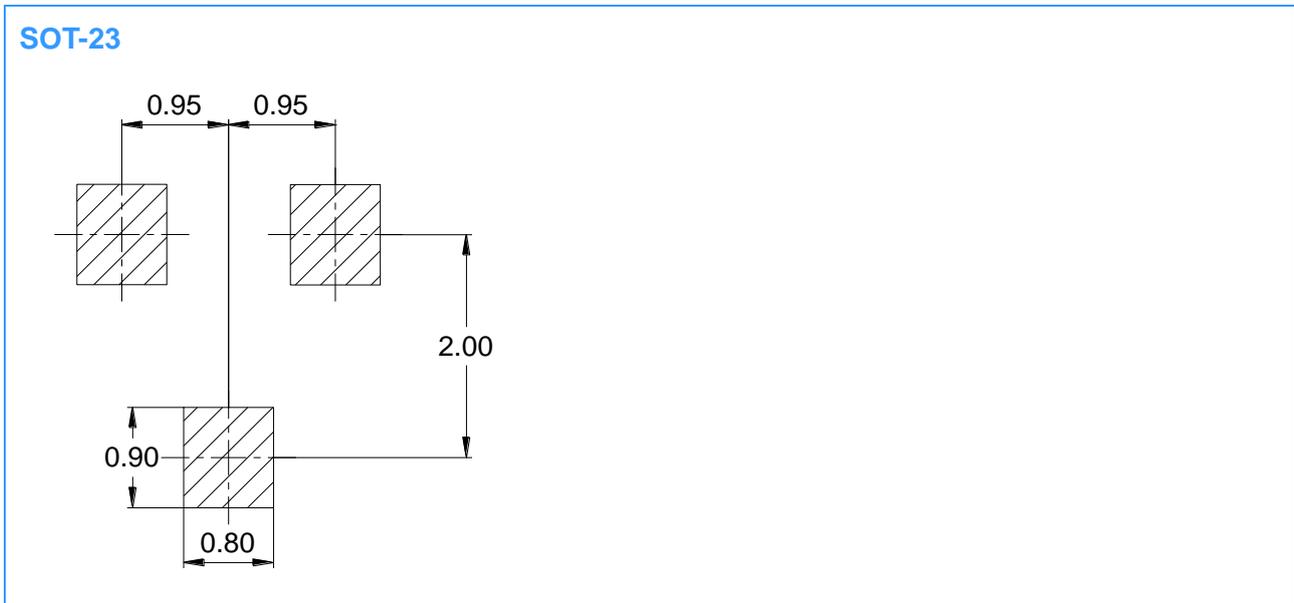


Fig 4 $V_{BE(on)}$ vs. I_C

Package Outline Dimensions (Unit: mm)



Package Outline Dimensions (Unit: mm)



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